

E151 Lecture 6 – BJTs in Circuits & PNP

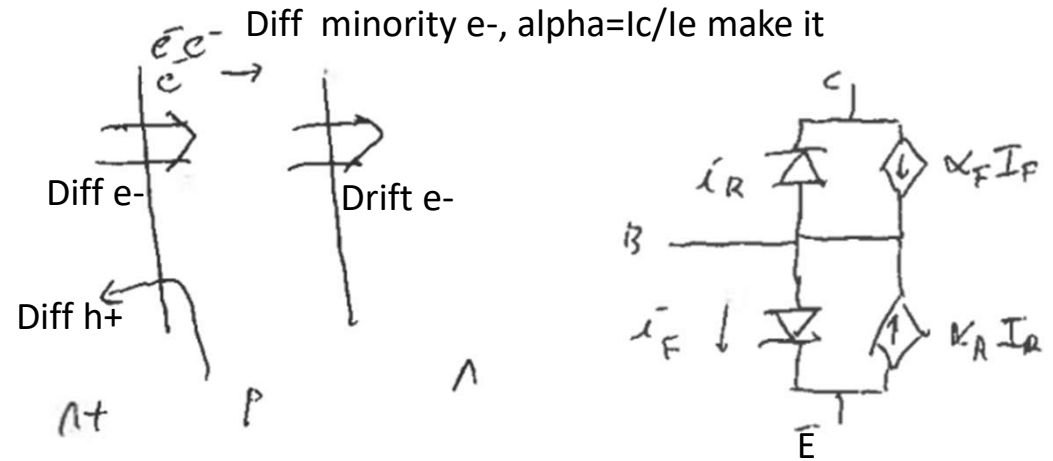
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Disclaimer

These are notes for Prof. Spencer to give the lecture, they were not intended as a reference for students. Students asked for them anyway, so I'm putting them up as a courtesy. Remember that they are not intended as a substitute for lecture.

Introduced BJTs Last Time

- Like two diodes, but short base region steals current sometimes
- Started with device picture → Ebers-Moll (computer) model
- Now, go from Ebers-Moll to useful models:
 - Picture
 - Equivalent circuits
 - Small signal models



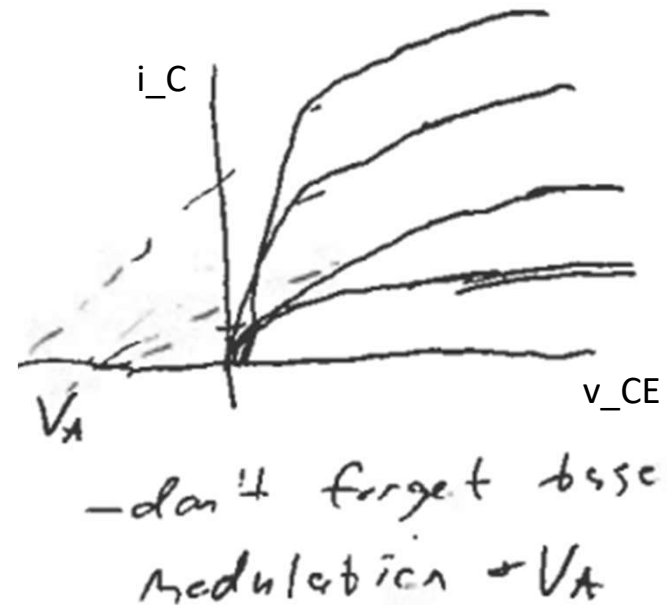
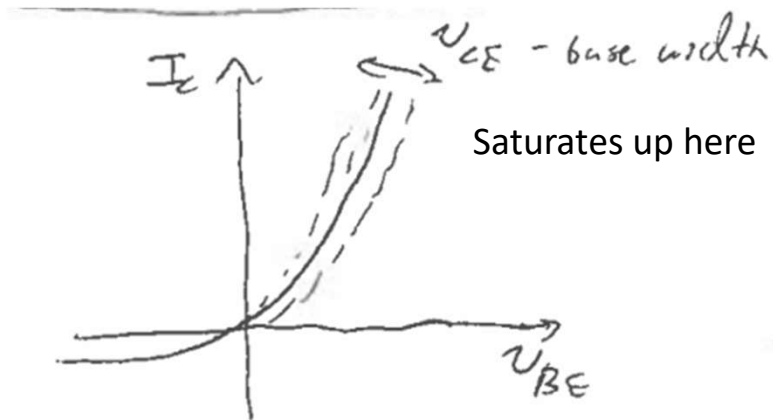
$$I_C = I_S \left(e^{V_{BC}/\phi_{TH}} - 1 \right) - \frac{I_S}{\alpha_R} \left(e^{V_{BC}/\phi_{TH}} - 1 \right)$$

$$I_E = I_S \left(e^{V_{BC}/\phi_{TH}} - 1 \right) - \frac{I_S}{\alpha_F} \left(e^{V_{BE}/\phi_{TH}} - 1 \right)$$

Note: $I_{ES} = \alpha * I_{CS}$, simplify to one I_S

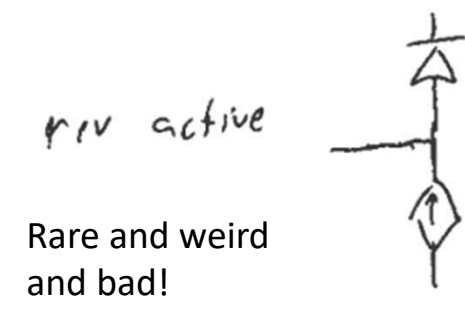
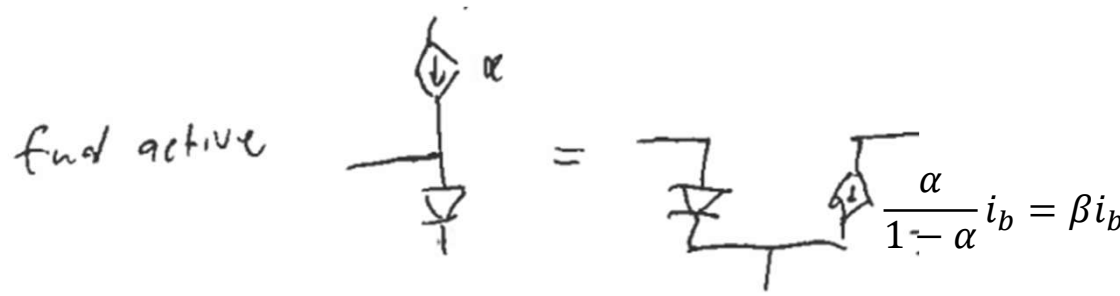
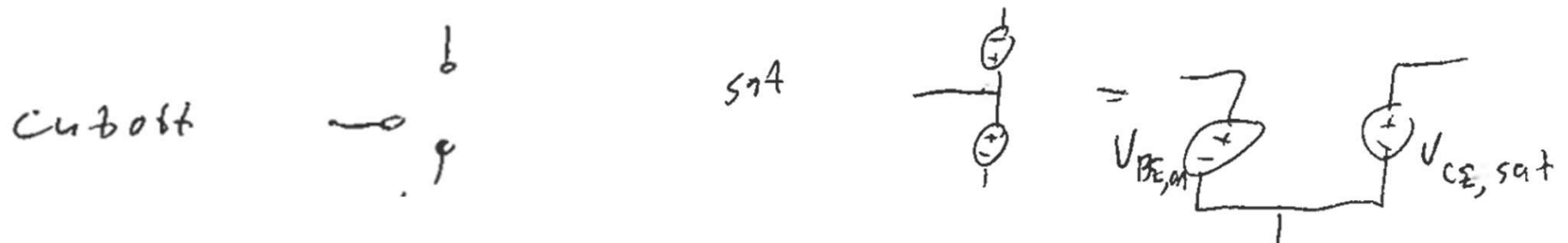
Pictures – i_C - v_{BE} , i_C - v_{CE}

- Two different ways to look at things
- Omitting breakdown on these graphs
- i_B - v_{BE} is identical to i_C - v_{BE}



Circuit Models in Regions of Operation

- Specify each region in terms of BE jn on/off and BE jn on/off
- Link to what is on in Ebers-Moll, clarify hitting $V_{CE,SAT}$ → saturated



Exercise: finding regions of operation

- Basically a CE configuration w/ impractical bias
 - $E=0V$,
 - $B=100k+V_B$,
 - $C=1k+V_C$,
 - $\beta=100$,
 - $V_{CESAT}=0.1V$,
 - $V_{BE_ON}=0.7V$
- Find I_C if $V_B = \{0.6V, 3.2V, 5.7V\}$ and $V_C = 5V$
- Possible to saturate yourself!